

MITSUBISHI HIGH SPEED CMOS M74HC4049BP/FP/DP

HEX INVERTING BUFFER/LOGIC-LEVEL DOWN CONVERTER

DESCRIPTION

The M74HC4049B is a semiconductor integrated circuit consisting of 6 built-in buffer/converter circuits with inverting outputs.

FEATURES

- High-speed: 12ns typ. ($C_L=50\text{pF}$, $V_{CC}=5\text{V}$)
- Low power dissipation: $5\mu\text{W}/\text{package}$, max ($V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$, quiescent state)
- High noise margin: 30% of V_{CC} , min ($V_{CC}=4.5\text{V}$, 6V)
- Capable of driving 15 74LSTTL loads
- Wide operating voltage range: $V_{CC}=2\sim 6\text{V}$
- Wide operating temperature range: $T_a=-40\sim +85^\circ\text{C}$

APPLICATION

General purpose, for use in industrial and consumer digital equipment.

FUNCTIONAL DESCRIPTION

Use of silicon gate technology allows the M74HC4049B to maintain the low power dissipation and high noise margin characteristics of the standard CMOS logic 4000B series while giving high-speed performance equivalent to the LSTTL.

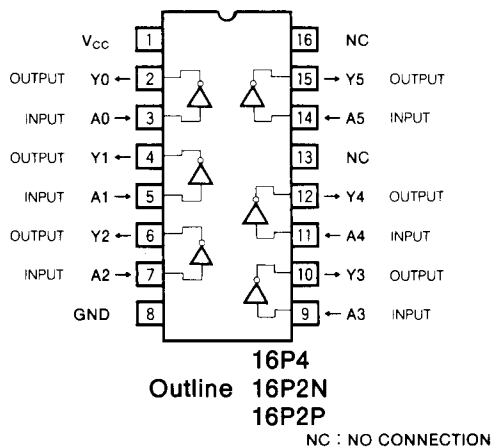
Unlike ordinary input protection circuits, inputs can be applied up to $\text{GND}+15\text{V}$, irrespective of V_{CC} , allowing the circuit to be used as logic-level converter from CMOS to high-speed CMOS/LSTTL logic circuits.

When input A is high, the output Y will become low, and when input A is low, the output Y will become high.

FUNCTION TABLE

| Input | Output |
|-------|--------|
| A | Y |
| L | H |
| H | L |

PIN CONFIGURATION (TOP VIEW)



LOGIC DIAGRAM (EACH BUFFER)



ABSOLUTE MAXIMUM RATINGS ($T_a = -40\sim +85^\circ\text{C}$, unless otherwise noted)

| Symbol | Parameter | Conditions | Ratings | Unit |
|-----------|--------------------------------|----------------------|-----------------------|------------------|
| V_{CC} | Supply voltage | | $-0.5\sim +7.0$ | V |
| V_I | Input voltage | | $-0.5\sim +18$ | V |
| V_O | Output voltage | | $-0.5\sim V_{CC}+0.5$ | V |
| I_{IK} | Input protection diode current | $V_I < 0\text{V}$ | 20 | mA |
| I_{OK} | Output parasitic diode current | $V_O < 0\text{V}$ | 20 | mA |
| I_O | Output current per output pin | $V_O > V_{CC}$ | 20 | mA |
| I_{CC} | Supply/GND current | V_{CC}, GND | ± 35 | mA |
| P_d | Power dissipation | (Note 1) | ± 75 | mW |
| T_{stg} | Storage temperature range | | 500 | $^\circ\text{C}$ |
| | | | $-65\sim +150$ | |

Note 1 : M74HC4049BFP, $T_a = -40\sim +70^\circ\text{C}$ and $T_a = 70\sim 85^\circ\text{C}$ are derated at $-6\text{mW}/^\circ\text{C}$
M74HC4049BDP, $T_a = -40\sim +50^\circ\text{C}$ and $T_a = 50\sim 85^\circ\text{C}$ are derated at $-5\text{mW}/^\circ\text{C}$

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RECOMMENDED OPERATING CONDITIONS ($T_a = -40 \sim +85^\circ\text{C}$)

| Symbol | Parameter | Limits | | | Unit |
|------------|-----------------------------|------------------------|-----|----------|------------------|
| | | Min | Typ | Max | |
| V_{CC} | Supply voltage | 2 | | 6 | V |
| V_I | Input voltage | 0 | | 15 | V |
| V_O | Output voltage | 0 | | V_{CC} | V |
| T_{opr} | Operating temperature range | -40 | | +85 | $^\circ\text{C}$ |
| t_r, t_f | Input risetime, falltime | $V_{CC} = 2.0\text{V}$ | 0 | 1000 | ns |
| | | $V_{CC} = 4.5\text{V}$ | 0 | 500 | |
| | | $V_{CC} = 6.0\text{V}$ | 0 | 400 | |

ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Test conditions | Limits | | | | | | Unit | |
|----------|---------------------------|---|---------------------------|---------------------|------|------|---------------------------------|------|---------------|---|
| | | | $V_{CC}(\text{V})$ | 25 $^\circ\text{C}$ | | | -40 \sim +85 $^\circ\text{C}$ | | | |
| | | | | Min | Typ | Max | Min | Max | | |
| V_{IH} | High-level input voltage | $V_O = 0.1\text{V}$ $ I_O = 20\mu\text{A}$ | 2.0 | 1.5 | | | 1.5 | | V | |
| | | | 4.5 | 3.15 | | | 3.15 | | | |
| | | | 6.0 | 4.2 | | | 4.2 | | | |
| V_{IL} | Low-level input voltage | $V_O = V_{CC} - 0.1\text{V}$ $ I_O = 20\mu\text{A}$ | 2.0 | | | 0.5 | | 0.5 | V | |
| | | | 4.5 | | | 1.35 | | 1.35 | | |
| | | | 6.0 | | | 1.8 | | 1.8 | | |
| V_{OH} | High-level output voltage | $V_I = V_{IL}$ | $I_{OH} = -20\mu\text{A}$ | 2.0 | 1.9 | | | 1.9 | V | |
| | | | $I_{OH} = -20\mu\text{A}$ | 4.5 | 4.4 | | | 4.4 | | |
| | | | $I_{OH} = -20\mu\text{A}$ | 6.0 | 5.9 | | | 5.9 | | |
| | | | $I_{OH} = -6.0\text{mA}$ | 4.5 | 4.18 | | | 4.13 | | |
| | | | $I_{OH} = -7.8\text{mA}$ | 6.0 | 5.68 | | | 5.63 | | |
| V_{OL} | Low-level output voltage | $V_I = V_{IH}$ | $I_{OL} = 20\mu\text{A}$ | 2.0 | | | 0.1 | | 0.1 | V |
| | | | $I_{OL} = 20\mu\text{A}$ | 4.5 | | | 0.1 | | 0.1 | |
| | | | $I_{OL} = 20\mu\text{A}$ | 6.0 | | | 0.1 | | 0.1 | |
| | | | $I_{OL} = 6.0\text{mA}$ | 4.5 | | | 0.26 | | 0.33 | |
| | | | $I_{OL} = 7.8\text{mA}$ | 6.0 | | | 0.26 | | 0.33 | |
| I_{IH} | High-level input current | $V_I = 6\text{V}$ | 6.0 | | | 0.1 | | 1.0 | μA | |
| | | $V_I = 15\text{V}$ | 6.0 | | | 0.5 | | 5.0 | | |
| I_{IL} | Low-level input current | $V_I = 0\text{V}$ | 6.0 | | | -0.1 | | -1.0 | μA | |
| I_{CC} | Quiescent supply current | $V_I = 15\text{V}, \text{GND}, I_O = 0\mu\text{A}$ | 6.0 | | | 1.0 | | 10.0 | μA | |

SWITCHING CHARACTERISTICS ($V_{CC} = 5\text{V}, T_a = 25^\circ\text{C}$)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|-----------|---|------------------------------|--------|-----|-----|------|
| | | | Min | Typ | Max | |
| t_{FLH} | Low-level to high-level and high-level to low-level output transition time | $C_L = 50\text{pF}$ (Note 3) | | | 10 | ns |
| t_{THL} | | | | | 10 | |
| t_{PLH} | Low-level to high-level and high-level to low-level output propagation time | | | | 15 | ns |
| t_{PHL} | | | | | 15 | |

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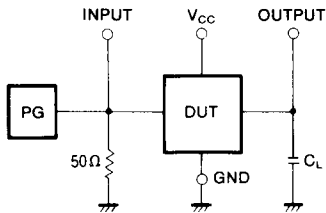
HEX INVERTING BUFFER/LOGIC-LEVEL DOWN CONVERTER

SWITCHING CHARACTERISTICS ($V_{CC} = 2\sim 6V$, $T_a = -40\sim +85^\circ C$)

| Symbol | Parameter | Test conditions | Limits | | | | | Unit | |
|-----------|---|-----------------------|-------------|-----|-----|-----------|-----|------|----|
| | | | 25°C | | | -40~+85°C | | | |
| | | | $V_{CC}(V)$ | Min | Typ | Max | Min | Max | |
| t_{TLH} | Low-level to high-level and high-level to low-level output transition time | $C_L = 50pF$ (Note 3) | 2.0 | | | 60 | | 75 | ns |
| | | | 4.5 | | | 12 | | 15 | |
| | | | 6.0 | | | 10 | | 13 | |
| t_{THL} | | | 2.0 | | | 60 | | 75 | ns |
| | | | 4.5 | | | 12 | | 15 | |
| | | | 6.0 | | | 10 | | 13 | |
| t_{PLH} | | $C_L = 50pF$ (Note 3) | 2.0 | | | 85 | | 100 | ns |
| | | | 4.5 | | | 17 | | 20 | |
| | | | 6.0 | | | 15 | | 18 | |
| t_{PHL} | Low-level to high-level and high-level to low-level output propagation time | | 2.0 | | | 75 | | 95 | ns |
| | | | 4.5 | | | 15 | | 19 | |
| | | | 6.0 | | | 13 | | 16 | |
| t_{PLH} | | $C_L = 50pF$ (Note 3) | 2.0 | | | 127 | | 150 | ns |
| | | | 4.5 | | | 25 | | 30 | |
| | | | 6.0 | | | 22 | | 27 | |
| t_{PHL} | | | 2.0 | | | 112 | | 142 | ns |
| | | | 4.5 | | | 22 | | 28 | |
| | | | 6.0 | | | 19 | | 24 | |
| C_i | input capacitance | | | | | | | 10 | pF |
| C_{PD} | Power dissipation capacitance (Note 2) | | | | 34 | | | | pF |

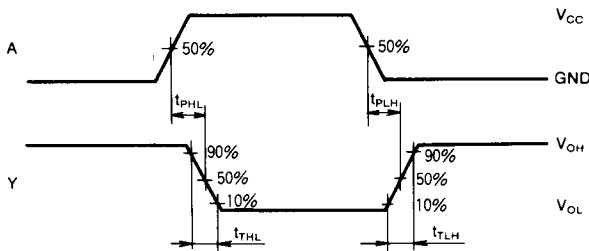
Note 2 : C_{PD} is the internal capacitance of the IC calculated from operation supply current under no-load conditions. (per buffer)
The power dissipated during operation under no-load conditions is calculated using the following formula:
 $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_i + I_{CC} \cdot V_{CC}$

Note 3 : Test Circuit



- (1) The pulse generator (PG) has the following characteristics (10%~90%): $t_r = 6ns$, $t_f = 6ns$
- (2) The capacitance C_L includes stray wiring capacitance and the probe input capacitance.

TIMING DIAGRAM



MITSUBISHI HIGH SPEED CMOS
PACKAGE OUTLINES

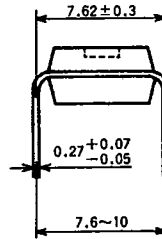
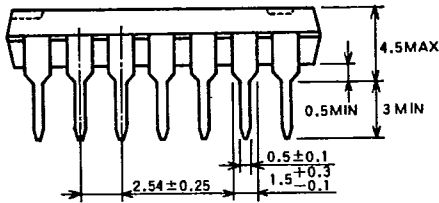
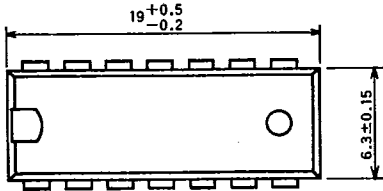
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91D 12849

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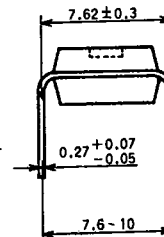
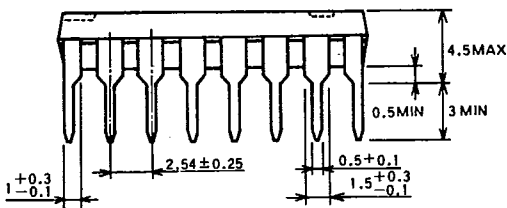
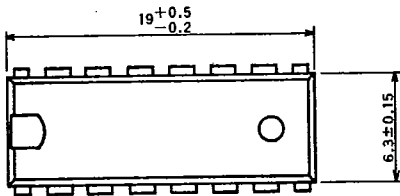
TYPE 14P4 14-PIN MOLDED PLASTIC DIP

Dimension in mm



TYPE 16P4 16-PIN MOLDED PLASTIC DIP

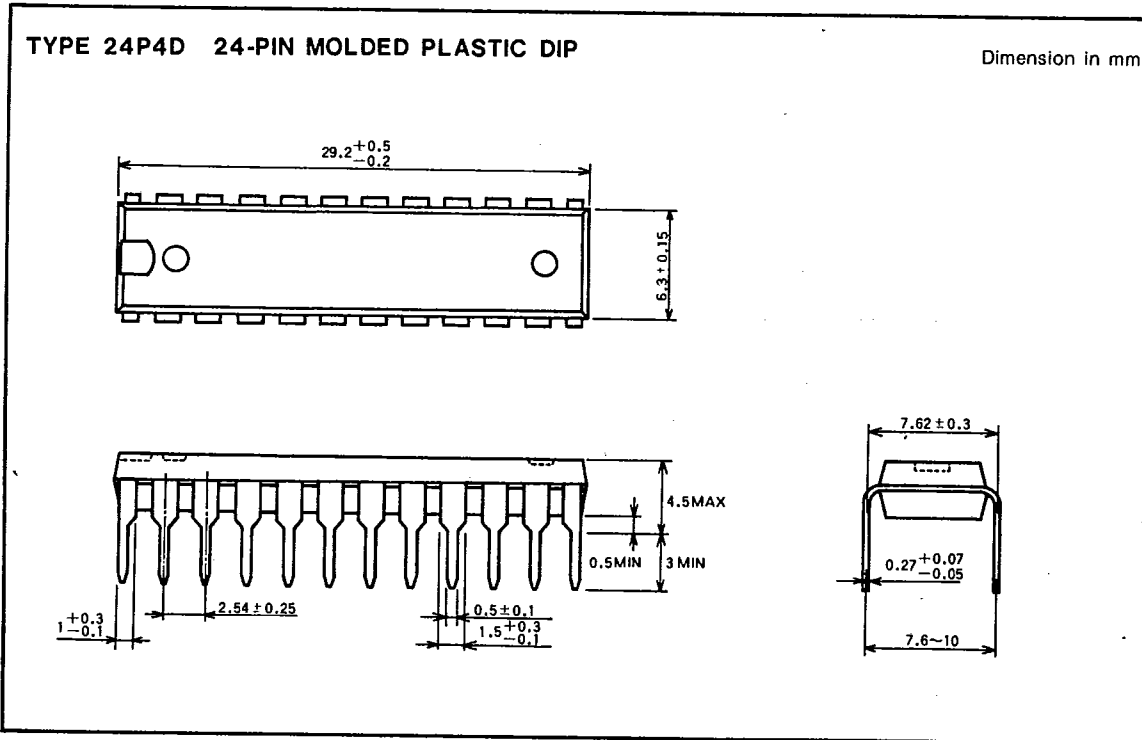
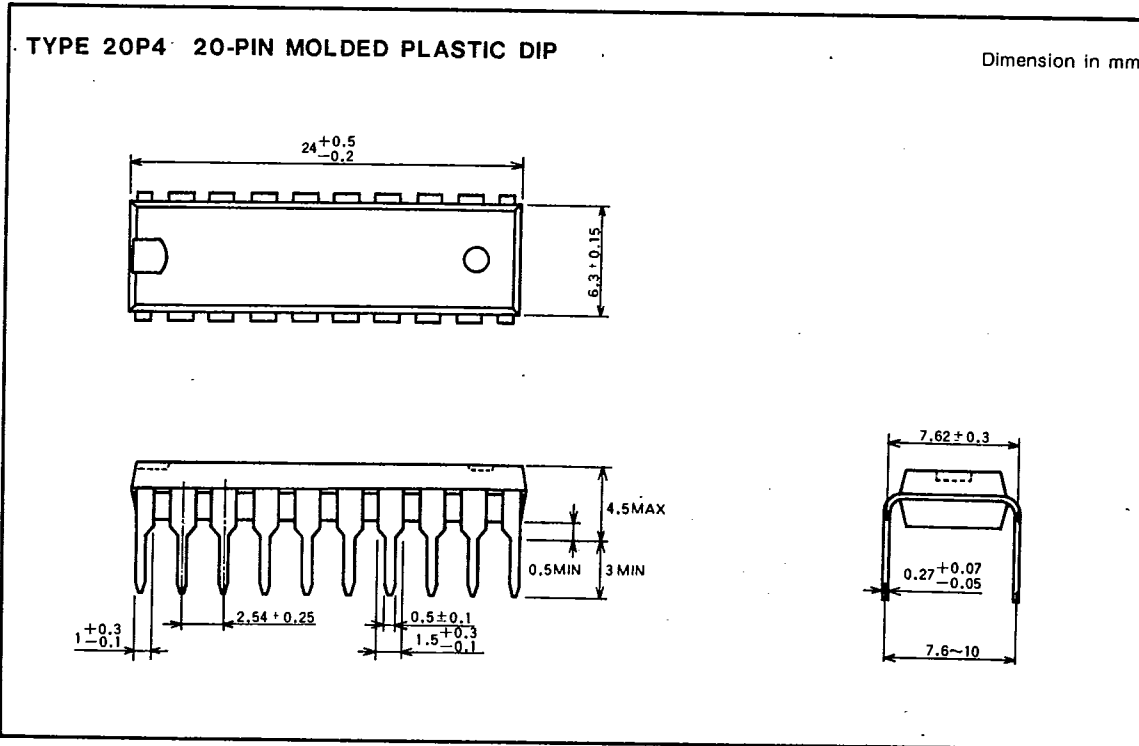
Dimension in mm



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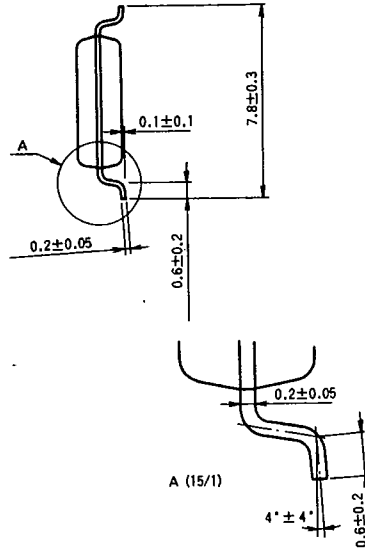
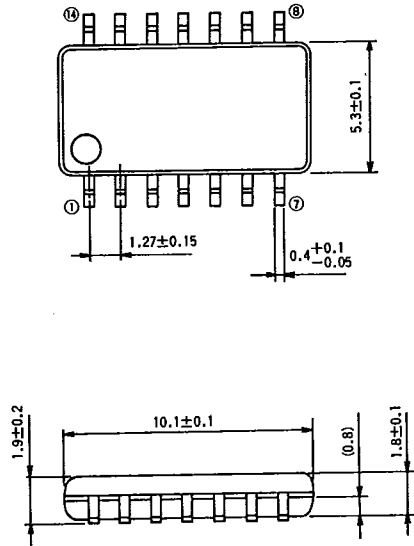
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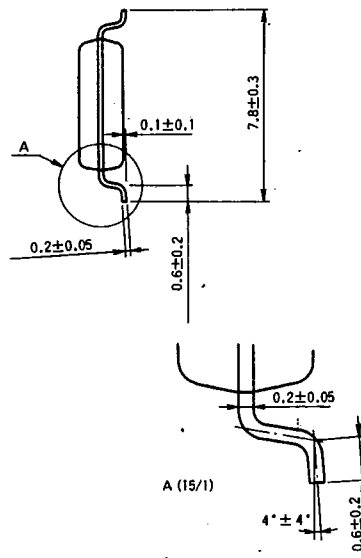
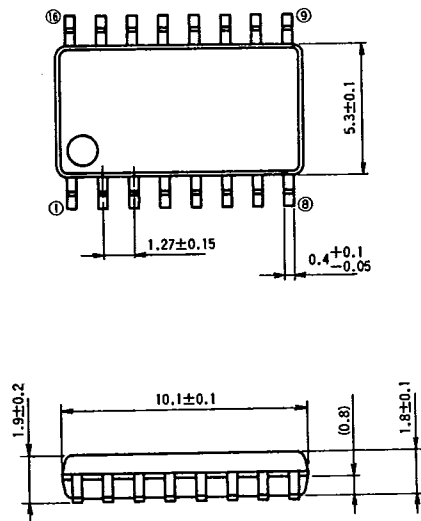
TYPE 14P2N 14PIN MOLDED PLASTIC SOP

Dimension in mm



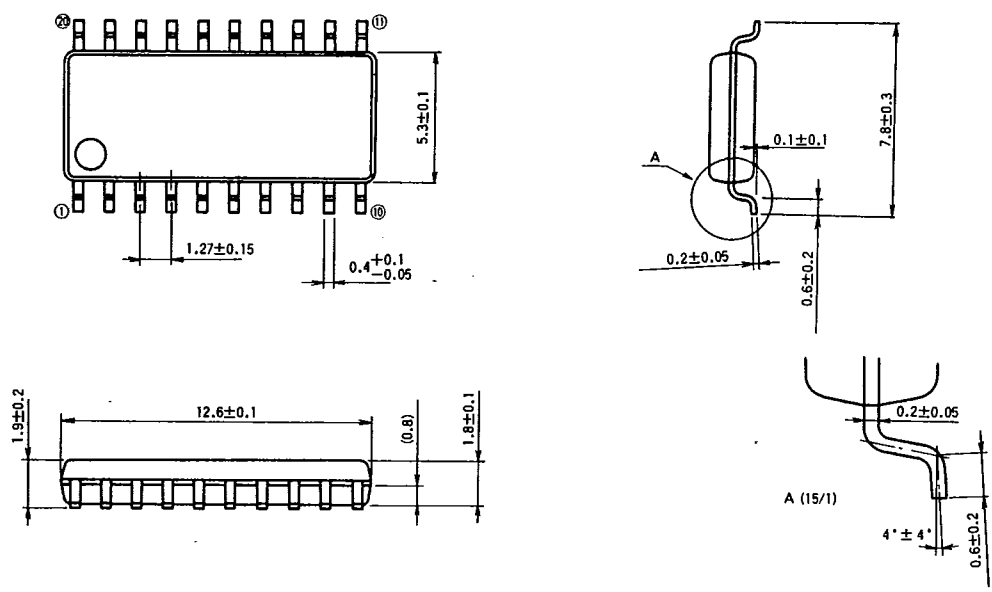
TYPE 16P2N 16PIN MOLDED PLASTIC SOP

Dimension in mm



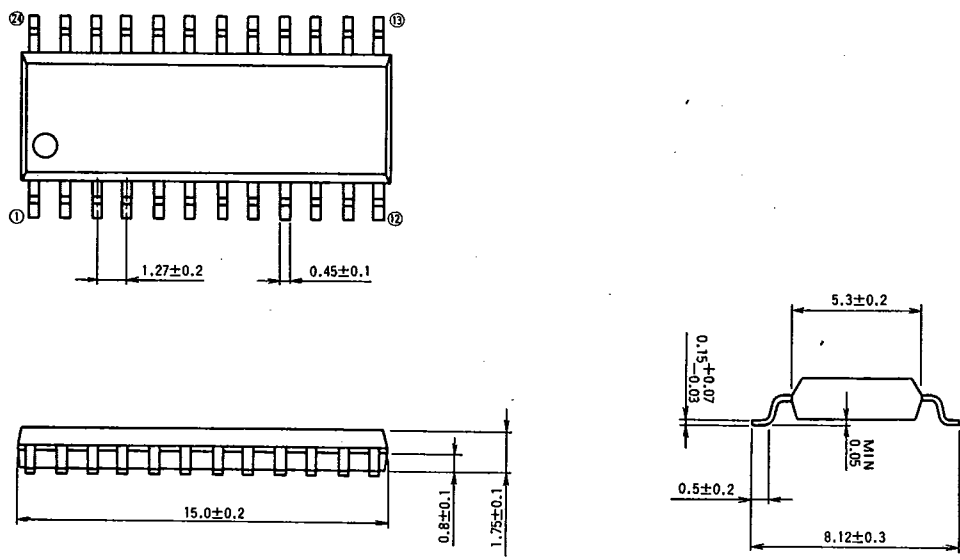
TYPE 20P2N 20PIN MOLDED PLASTIC SOP

Dimension in mm



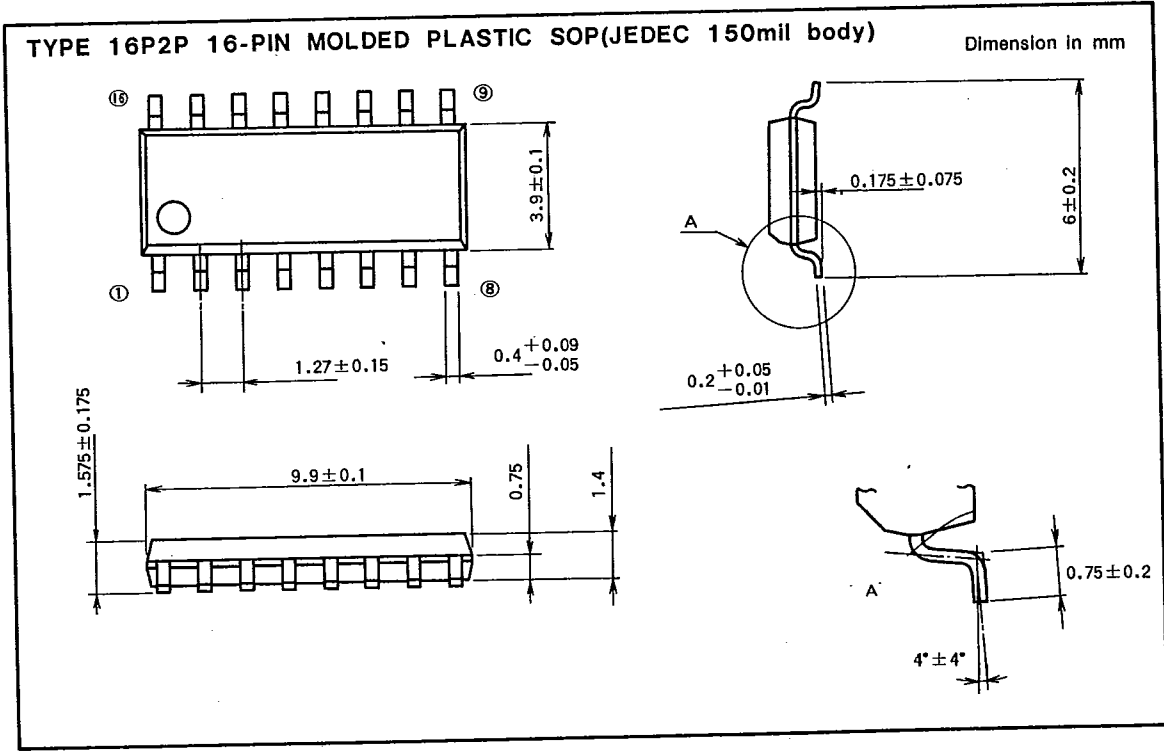
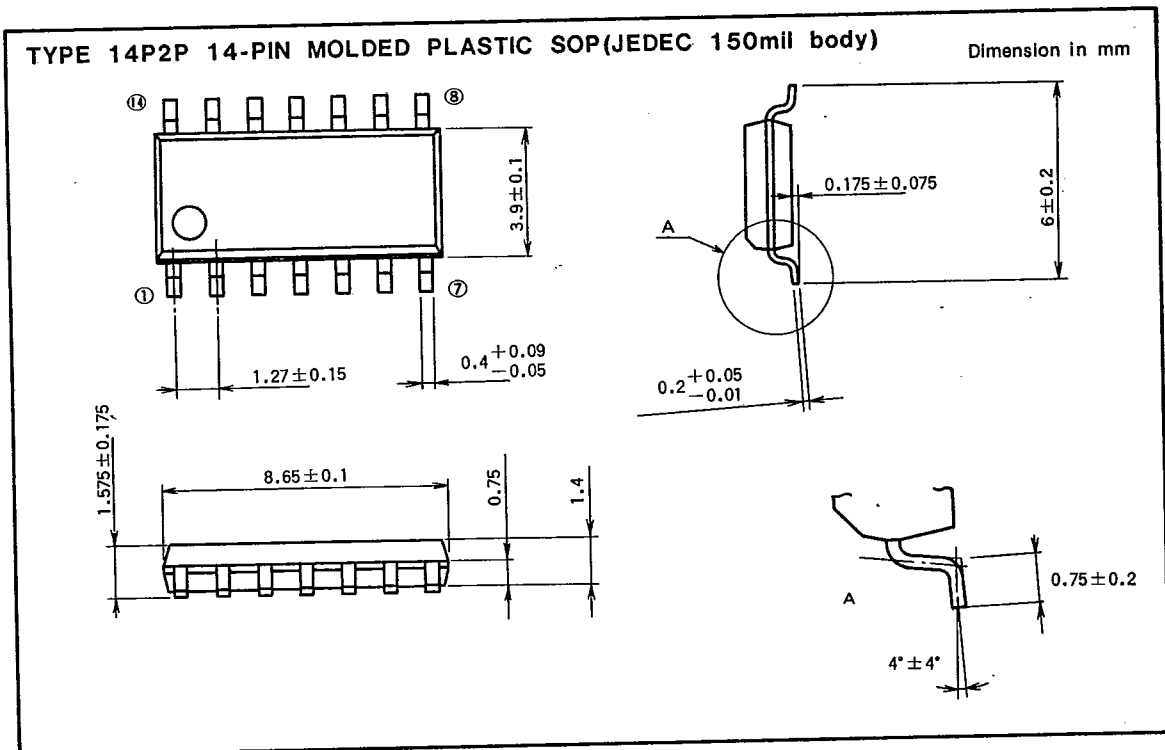
TYPE 24P2 24PIN MOLDED PLASTIC SOP

Dimension in mm



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